

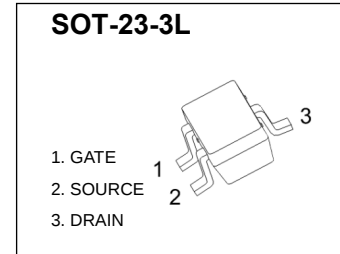


JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

## SOT-23-3L Plastic-Encapsulate MOSFETS

### **CJK3400** N-Channel Enhancement Mode Field Effect Transistor

| $V_{(BR)DSS}$ | $R_{DS(on)MAX}$    | $I_D$ |
|---------------|--------------------|-------|
| 30V           | 35m $\Omega$ @ 10V | 5.8A  |
|               | 40m $\Omega$ @4.5V |       |
|               | 52m $\Omega$ @2.5V |       |



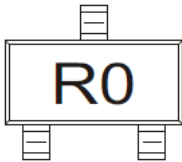
#### FEATURE

- High dense cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

#### APPLICATION

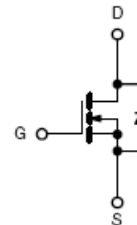
- Load/Power Switching
- Interfacing Switching

#### MARKING



R0=Device code

#### Equivalent Circuit



#### Maximum ratings ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

| Parameter                                                | Symbol          | Value    | Unit                 |
|----------------------------------------------------------|-----------------|----------|----------------------|
| Drain-Source Voltage                                     | $V_{DS}$        | 30       | V                    |
| Gate-Source Voltage                                      | $V_{GS}$        | $\pm 12$ | V                    |
| Continuous Drain Current                                 | $I_D$           | 5.8      | A                    |
| Drain Current-Pulsed <sup>①</sup>                        | $I_{DM}$        | 30       | A                    |
| Power Dissipation <sup>④</sup>                           | $P_D$           | 1.25     | W                    |
| Thermal Resistance from Junction to Ambient <sup>④</sup> | $R_{\theta JA}$ | 100      | $^{\circ}\text{C/W}$ |
| Operation Junction and Storage Temperature Range         | $T_J, T_{STG}$  | -55~+150 | $^{\circ}\text{C}$   |

# MOSFET ELECTRICAL CHARACTERISTICS

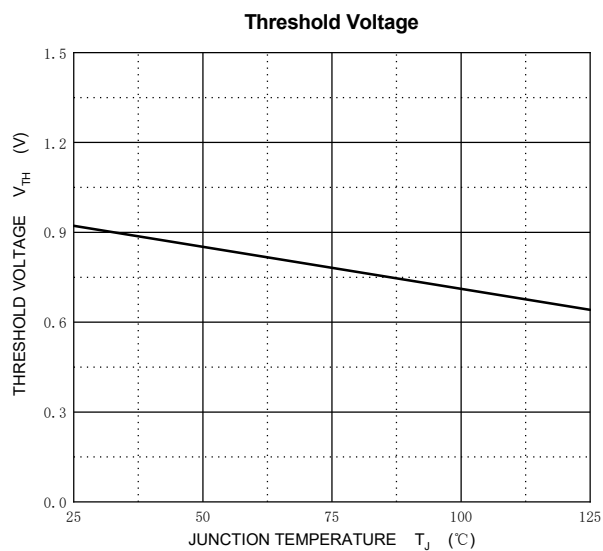
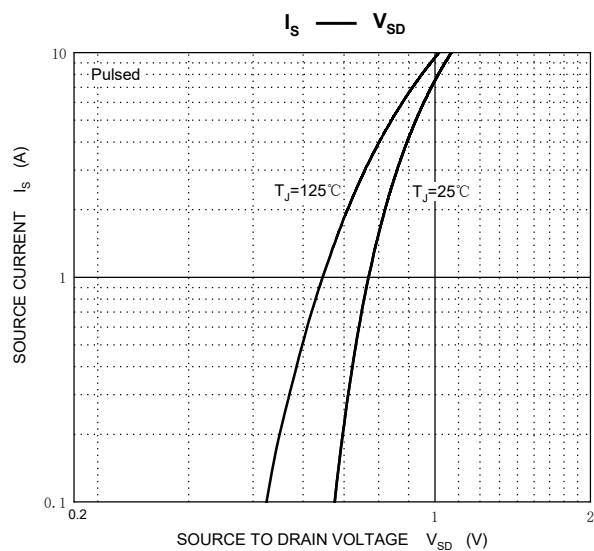
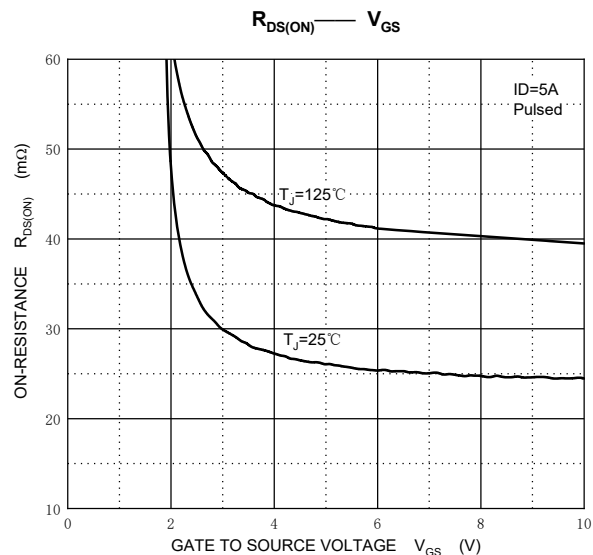
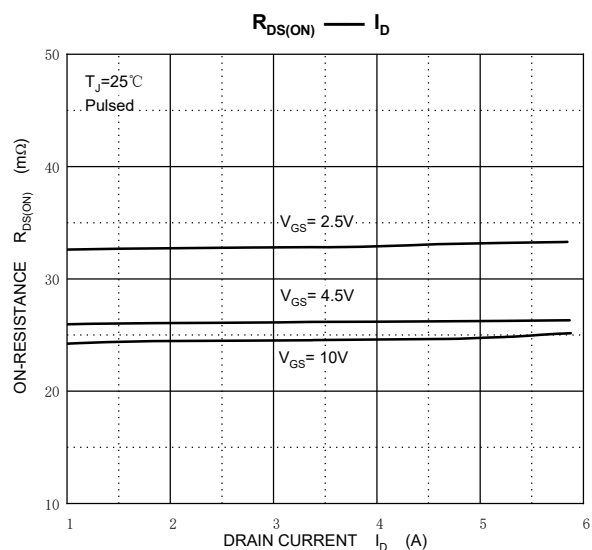
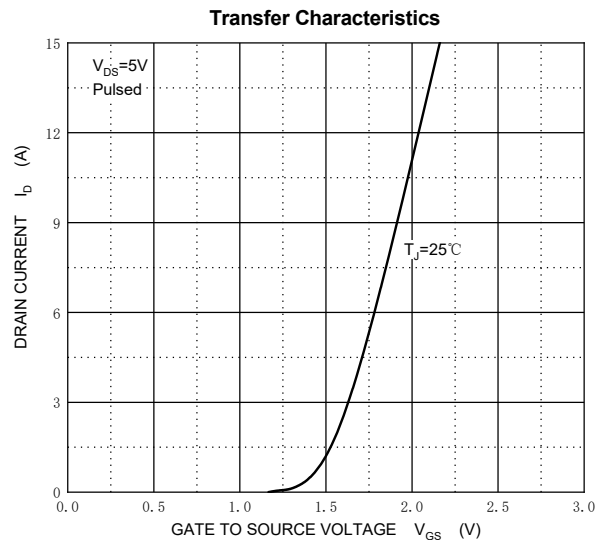
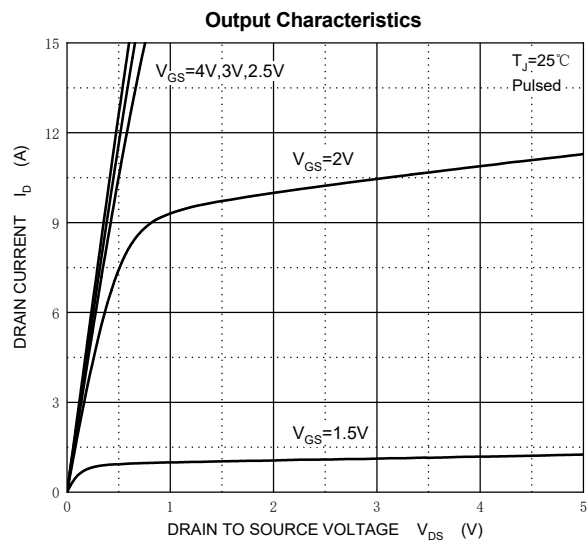
T<sub>a</sub>=25 °C unless otherwise specified

| Parameter                                              | Symbol                | Test Condition                                                                            | Min | Typ | Max  | Unit |
|--------------------------------------------------------|-----------------------|-------------------------------------------------------------------------------------------|-----|-----|------|------|
| Off Characteristics                                    |                       |                                                                                           |     |     |      |      |
| Drain-source breakdown voltage                         | V <sub>(BR) DSS</sub> | V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA                                               | 30  |     |      | V    |
| Zero gate voltage drain current                        | I <sub>DSS</sub>      | V <sub>DS</sub> =24V, V <sub>GS</sub> = 0V, T <sub>J</sub> =25℃                           |     |     | 1    | μA   |
|                                                        |                       | V <sub>DS</sub> =24V, V <sub>GS</sub> = 0V, T <sub>J</sub> =125℃                          |     |     | 1    | mA   |
| Gate-source leakage current                            | I <sub>GSS</sub>      | V <sub>GS</sub> =±12V, V <sub>DS</sub> = 0V                                               |     |     | ±100 | nA   |
| On characteristics                                     |                       |                                                                                           |     |     |      |      |
| Drain-source on-resistance ②                           | R <sub>DS(on)</sub>   | V <sub>GS</sub> =10V, I <sub>D</sub> =5.8A                                                |     | 25  | 35   | mΩ   |
|                                                        |                       | V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A                                                 |     | 27  | 40   | mΩ   |
|                                                        |                       | V <sub>GS</sub> =2.5V, I <sub>D</sub> =4A                                                 |     | 33  | 52   | mΩ   |
| Forward transconductance                               | g <sub>FS</sub>       | V <sub>DS</sub> =5V, I <sub>D</sub> =5A                                                   | 8   |     |      | S    |
| Gate threshold voltage                                 | V <sub>GS(th)</sub>   | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA                                  | 0.7 | 0.9 | 1.4  | V    |
| Dynamic Characteristics ③                              |                       |                                                                                           |     |     |      |      |
| Input capacitance                                      | C <sub>iss</sub>      | V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f =1MHz                                        |     | 820 | 1050 | pF   |
| Output capacitance                                     | C <sub>oss</sub>      |                                                                                           |     | 99  |      | pF   |
| Reverse transfer capacitance                           | C <sub>rss</sub>      |                                                                                           |     | 77  |      | pF   |
| Gate resistance                                        | R <sub>g</sub>        | V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f =1MHz                                         |     | 3.6 |      | Ω    |
| Switching Characteristics ③                            |                       |                                                                                           |     |     |      |      |
| Turn-on delay time                                     | t <sub>d(on)</sub>    | V <sub>GS</sub> =10V, V <sub>DS</sub> =15V,<br>R <sub>L</sub> =2.7Ω, R <sub>GEN</sub> =3Ω |     | 3.3 | 5    | ns   |
| Turn-on rise time                                      | t <sub>r</sub>        |                                                                                           |     | 4.8 | 7    | ns   |
| Turn-off delay time                                    | t <sub>d(off)</sub>   |                                                                                           |     | 26  | 40   | ns   |
| Turn-off fall time                                     | t <sub>f</sub>        |                                                                                           |     | 4   | 6    | ns   |
| Total Gate Charge                                      | Q <sub>g</sub>        | V <sub>DS</sub> =10V, I <sub>D</sub> =5A,<br>V <sub>GS</sub> =6V                          |     | 9.5 |      | nC   |
| Gate-Source Charge                                     | Q <sub>gs</sub>       |                                                                                           |     | 1.5 |      | nC   |
| Gate-Drain Charge                                      | Q <sub>gd</sub>       |                                                                                           |     | 3   |      | nC   |
| Drain-source diode characteristics and maximum ratings |                       |                                                                                           |     |     |      |      |
| Diode forward voltage ②                                | V <sub>SD</sub>       | I <sub>S</sub> =1A, V <sub>GS</sub> =0V                                                   |     |     | 1    | V    |
| Continuous drain-source diode forward current          | I <sub>S</sub>        |                                                                                           |     |     | 5.8  | A    |
| Pulsed drain-source diode forward current①             | I <sub>SM</sub>       |                                                                                           |     |     | 30   | A    |

## Note :

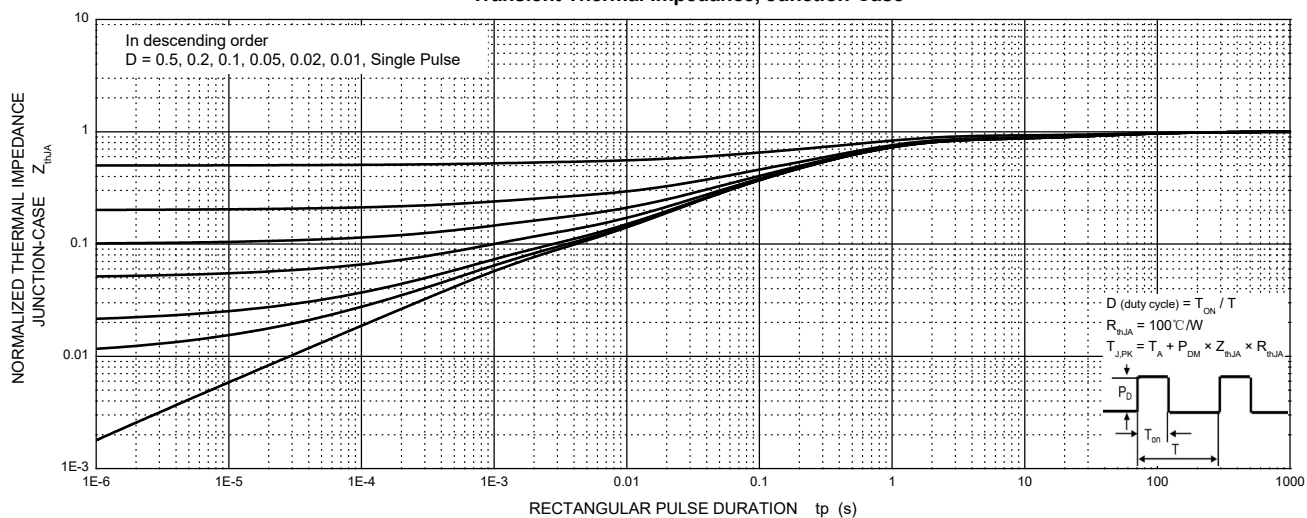
1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 2%.
3. Guaranteed by design, not subject to production testing.
4. The value of P<sub>D</sub>&R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, two sided, in a still air environment with T<sub>a</sub>=25 °C.

## Typical Characteristics

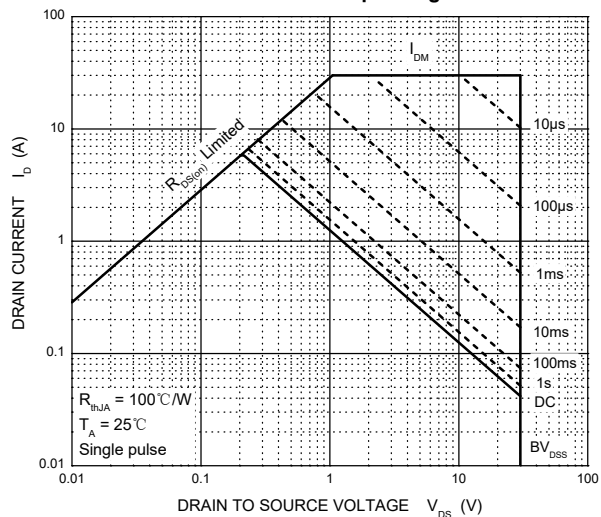


## Typical Characteristics

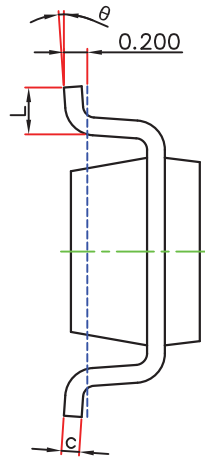
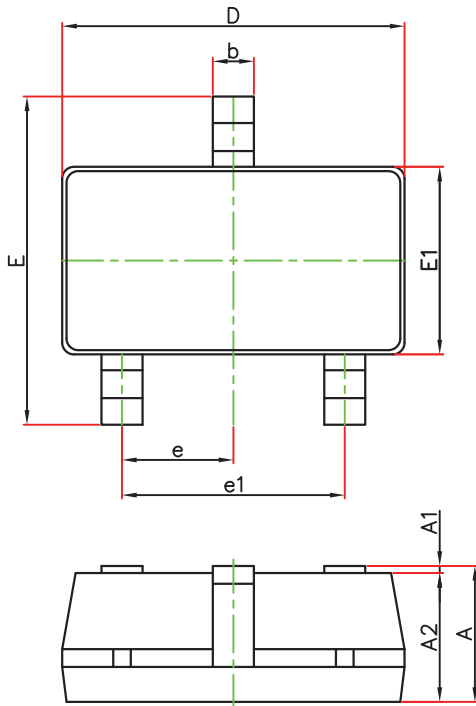
Transient Thermal Impedance, Junction-Case



Maximum Safe Operating Area

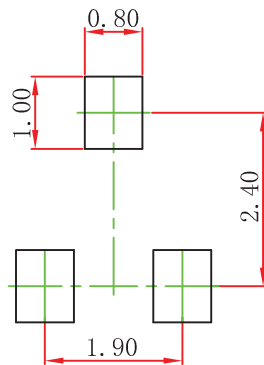


## SOT-23-3L Package Outline Dimensions



| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min.                      | Max.  | Min.                 | Max.  |
| A      | 1.050                     | 1.250 | 0.041                | 0.049 |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004 |
| A2     | 1.050                     | 1.150 | 0.041                | 0.045 |
| b      | 0.300                     | 0.500 | 0.012                | 0.020 |
| c      | 0.100                     | 0.200 | 0.004                | 0.008 |
| D      | 2.820                     | 3.020 | 0.111                | 0.119 |
| E1     | 1.500                     | 1.700 | 0.059                | 0.067 |
| E      | 2.650                     | 2.950 | 0.104                | 0.116 |
| e      | 0.950(BSC)                |       | 0.037(BSC)           |       |
| e1     | 1.800                     | 2.000 | 0.071                | 0.079 |
| L      | 0.300                     | 0.600 | 0.012                | 0.024 |
| θ      | 0°                        | 8°    | 0°                   | 8°    |

## SOT-23-3L Suggested Pad Layout



Note:

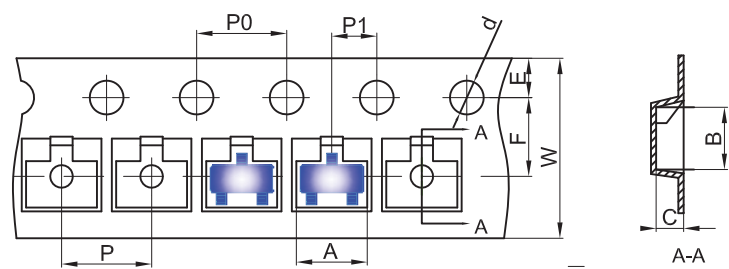
1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.

### NOTICE

JSCJ reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JSCJ does not assume any liability arising out of the application or use of any product described herein.

# SOT-23-3L Tape and Reel

## SOT-23-3L Embossed Carrier Tape

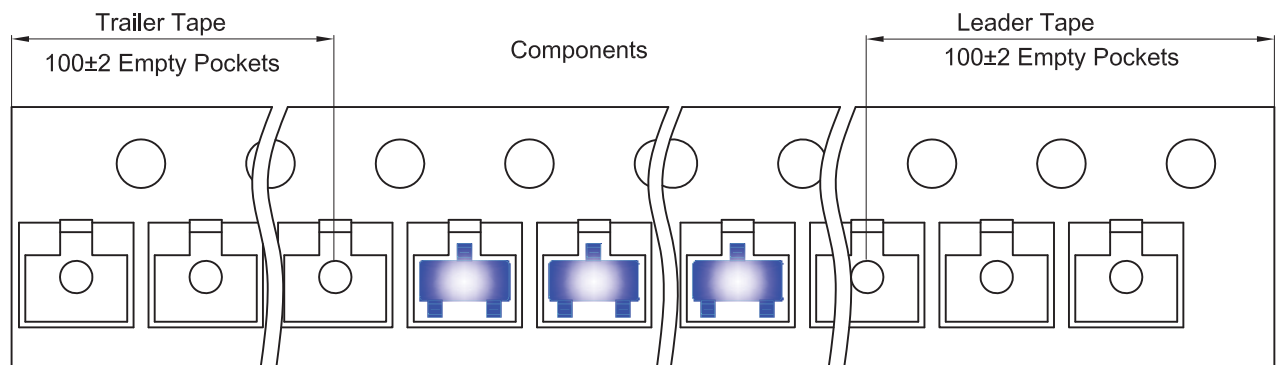


### Packaging Description:

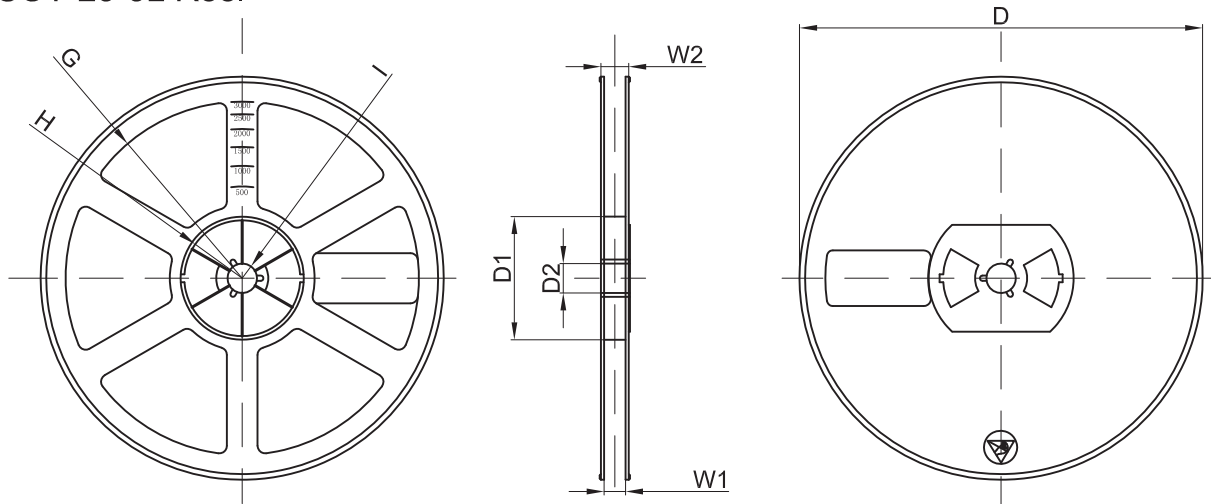
SOT-23-3L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 18.0cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

| Dimensions are in millimeter |      |      |      |       |      |      |      |      |      |      |
|------------------------------|------|------|------|-------|------|------|------|------|------|------|
| Pkg type                     | A    | B    | C    | d     | E    | F    | P0   | P    | P1   | W    |
| SOT-23-3L                    | 3.18 | 3.28 | 1.32 | Ø1.50 | 1.75 | 3.50 | 4.00 | 4.00 | 2.00 | 8.00 |

## SOT-23-3L Tape Leader and Trailer



## SOT-23-3L Reel



| Dimensions are in millimeter |         |       |       |        |        |       |      |       |
|------------------------------|---------|-------|-------|--------|--------|-------|------|-------|
| Reel Option                  | D       | D1    | D2    | G      | H      | I     | W1   | W2    |
| 7"Dia                        | Ø180.00 | 60.00 | 13.00 | R78.00 | R25.60 | R6.50 | 9.50 | 13.10 |

| REEL     | Reel Size | Box        | Box Size(mm) | Carton      | Carton Size(mm) | G.W.(kg) |
|----------|-----------|------------|--------------|-------------|-----------------|----------|
| 3000 pcs | 7 inch    | 30,000 pcs | 203×203×195  | 120,000 pcs | 438×438×220     |          |